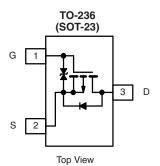




P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY								
V _{DS} (V)	$R_{DS(on)}(\Omega)$	V _{GS(th)} (V)	I _D (mA)	Q _g (Typ.)				
- 30	1.4 at V _{GS} = - 10 V	- 1.3 to - 3.0	- 385	1000				
	3.5 at $V_{GS} = -4.5$ V	- 1.3 to - 3.0	- 240	1000				



Marking Code: 2Kwll 2K = Part Number Code for TP0202K w =Week Code // = Lot Traceability

Ordering Information: TP0202K-T1-E3 (Lead (Pb)-free)

TP0202K-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

Halogen-free According to IEC 61249-2-21 Available



High-Side Switching

Low On-Resistance: 1.2 Ω (typ.)

Low Threshold: - 2 V (typ.)

Fast Swtiching Speed: 14 ns (typ.) Low Input Capacitance: 31 pF (typ.)

2000 V ESD Protection

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- **Battery Operated Systems**
- Power Supply Converter Circuits
- Solid-State Relays

BENEFITS

- · Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- **High-Speed Circuits**
- Easily Driven without Buffer

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage		V_{DS}	- 30	V			
Gate-Source Voltage		V _{GS}	± 20	v			
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _A = 25 °C	I_	- 385	mA			
Continuous Diain Current (1) = 150 °C)	T _A = 85 °C	I _D	- 280				
Pulsed Drain Current ^b		I _{DM}	- 750				
Davis Dissipation?	T _A = 25 °C	P _D	350	mW			
Power Dissipation ^a	T _A = 85 °C	ı D	185	11100			
Maximum Junction-to-Ambient ^a		R_{thJA}	350	°C/W			
Operating Junction and Storage Temperature Range		$T_{J_{I}}T_{stg}$	- 55 to 150	°C			

Notes:

- a. Surface Mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

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	Symbol	Test Conditions	Limits			
Parameter			Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -100 \mu\text{A}$	- 30	- 38		V
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.3	- 2	- 3.0	V
Coto Body Lookaga	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 50	nA
Gate-Body Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			± 300	
Zana Oata Wallana Busin O	1	V _{DS} = - 30 V, V _{GS} = 0 V			- 100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 85 °C			- 10	μΑ
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V, V _{DS} = - 10 V	- 500			mA
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 50 mA		2.1	3.5	Ω
Drain-Source On-Resistance ^a		V _{GS} = - 10 V, I _D = - 500 mA		1.25	1.4	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 200 mA		315		mS
Diode Forward Voltage ^a	V _{SD}	I _S = - 250 mA, V _{GS} = 0 V			- 1.2	V
Dynamic			•		•	
Total Gate Charge	Qg	V 16 V V 10 V		1000		pC
Gate-Source Charge	Q _{gs}	$V_{DS} = -16 \text{ V}, V_{GS} = -10 \text{ V}$ $I_{D} \cong -200 \text{ mA}$		225		
Gate-Drain Charge	Q _{gd}	10 = 200 m/r		175		
Input Capacitance	C _{iss}			31		pF
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1 MHz		11		
Reverse Transfer Capacitance	C _{rss}	1 = 1 WILLS		4		
Switching ^b			•	•	•	
Trans On Time	t _{d(on)}			9		
Turn-On Time	t _r	$V_{DD} = -15 \text{ V}, R_{L} = 75 \Omega$		6		nc
Turn Off Time	t _{d(off)}	$I_D \cong$ - 200 mA, V_{GEN} = - 10 V, R_G = 6 Ω		30		- ns
Turn-Off Time	t _f			20		

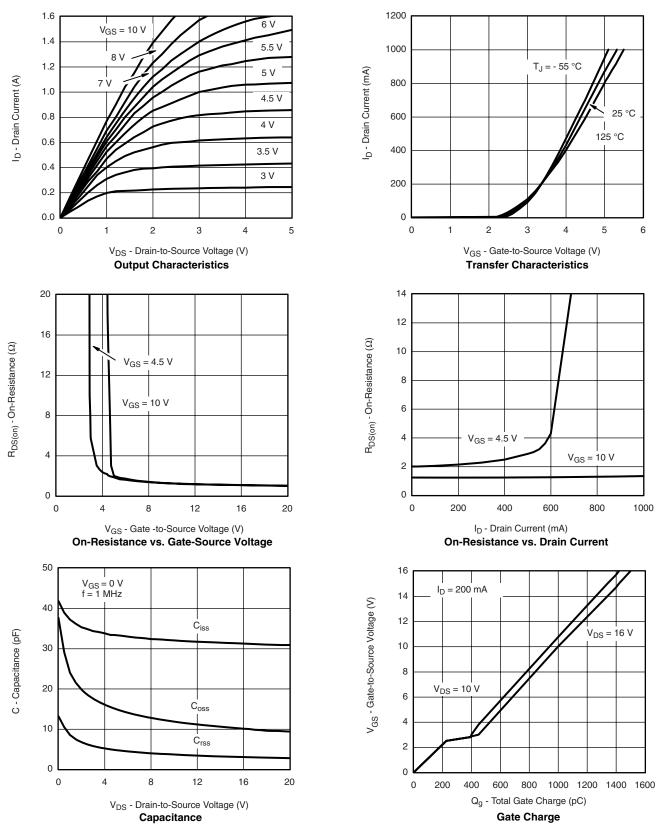
Notes:

- a. Pulse test: PW \leq 300 μs duty cycle \leq 2 %.
- b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



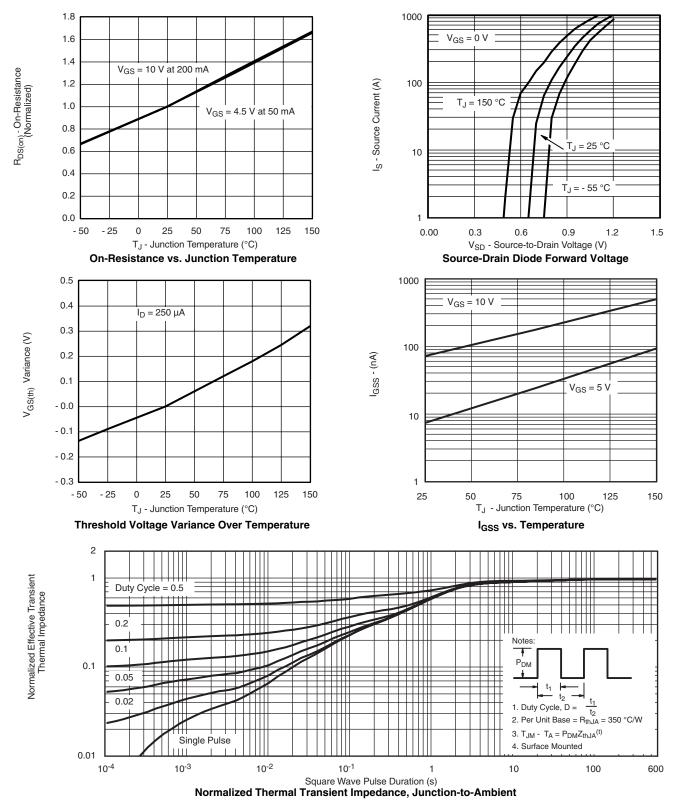
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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